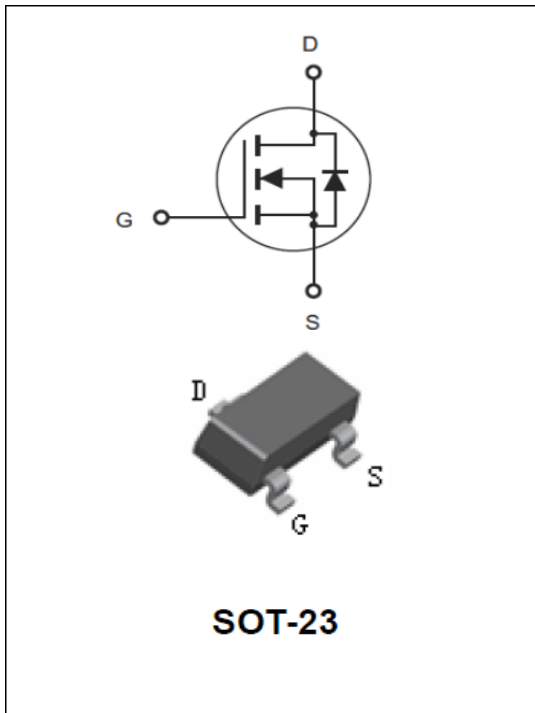


## N-Channel Enhancement Mode Field Effect Transistor



### Feature

- $V_{DS}=20V, I_D=4.5A$
- $R_{DS(ON)} < 25m\Omega @ V_{GS}=4.5V$
- $R_{DS(ON)} < 38m\Omega @ V_{GS}=2.5V$
- Epoxy meets UL 94 V-0 flammability rating
- Moisture Sensitivity Level1
- High density cell design for low  $R_{DS(ON)}$
- High Speed switching
- Rugged and reliable
- SOT-23 Package

### Application

- Battery protection
- Load switch
- Power management

### ■ Maximum Ratings ( $T_A=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source Voltage	20	V
$V_{GS}$	Gate-source Voltage	$\pm 10$	V
$I_D$	Drain Current	4.5	A
$I_{DM}$	Pulsed Drain Current	17	A
$P_D$	Total Power Dissipation	1	W
$R_{thJA}$	Thermal Resistance From Junction To Ambient	125	$^\circ C/W$
$T_J$	Operation Junction Temperature	-55~+150	$^\circ C$
$T_{STG}$	Storage Temperature	-55~+150	$^\circ C$

### ■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJL2300A	F2		3000	30000	120000	7" reel



# YJL2300A

## ■ Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
<b>Static Characteristics</b>						
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> =250μA	20			V
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V			1	μA
Gate-body leakage current	I <sub>GSS</sub>	V <sub>GS</sub> = ± 10V, V <sub>DS</sub> =0V			± 100	nA
Gate threshold voltage*	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> =250μA	0.5	0.7	0.9	V
Drain-source on-resistance*	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 4.5V, I <sub>D</sub> =4.5A		19.5	25	mΩ
		V <sub>GS</sub> = 2.5V, I <sub>D</sub> =4.0A		25	38	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> = 5V, I <sub>D</sub> =4.5A	5			s
<b>Dynamic Characteristics **</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V, f=1MHZ		482		pF
Output Capacitance	C <sub>oss</sub>			85		
Reverse Transfer Capacitance	C <sub>rss</sub>			52		
<b>Switching Characteristics**</b>						
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> =10V, V <sub>GS</sub> =4.5V, RL=2.8Ω, I <sub>D</sub> =1A, R <sub>GEN</sub> =6Ω		13		ns
Turn-on rise time	t <sub>r</sub>			54		
Turn-off delay time	t <sub>d(off)</sub>			18		
Turn-off Fall time	t <sub>f</sub>			11		
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =4.5A, V <sub>GS</sub> =4.5V		4.2		nC
Gate-Source Charge	Q <sub>gs</sub>			0.9		
Gate-Drain Charge	Q <sub>gd</sub>			1.4		
<b>Source-Drain Diode characteristics</b>						
Drain-Source Diode Forward Current	I <sub>S</sub>				4.5	A
Diode Forward voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =4.5A		0.8	1.2	V

Notes:

\*Pulse Test: Pulse Width ≤ 300μA, Duty Cycle ≤ 2%.

\*\*These parameters have no way to verify.

## ■ Characteristics (Typical)

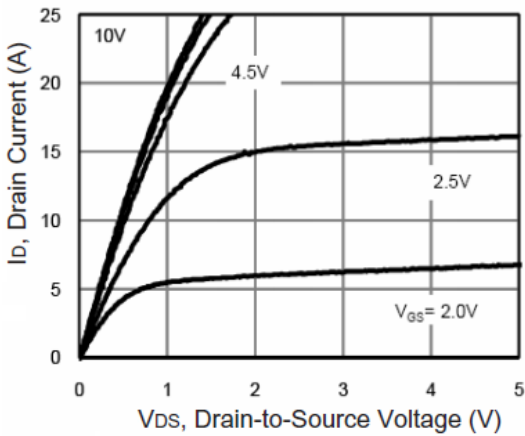


Figure 1. Output Characteristics

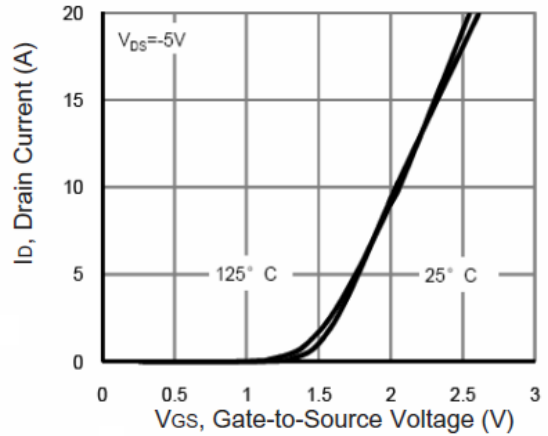


Figure 2. Transfer Characteristics

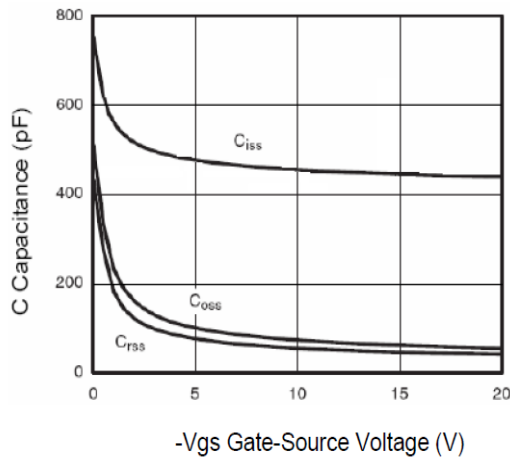


Figure 3. Capacitance

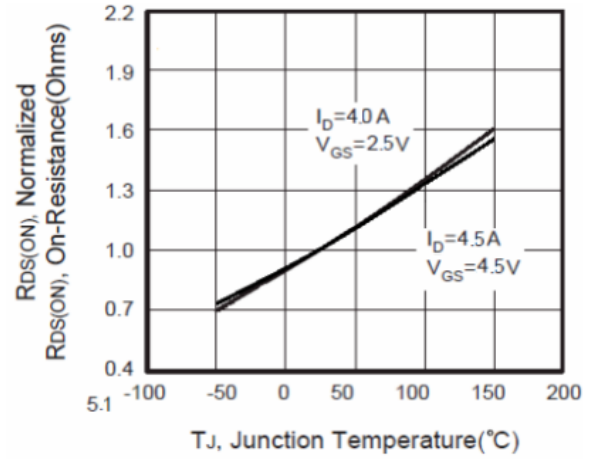


Figure 4. On-Resistance Variation with Temperature

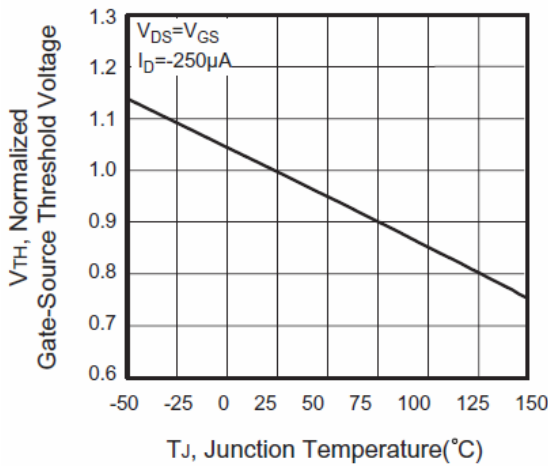


Figure 5. Gate Threshold Variation with Temperature

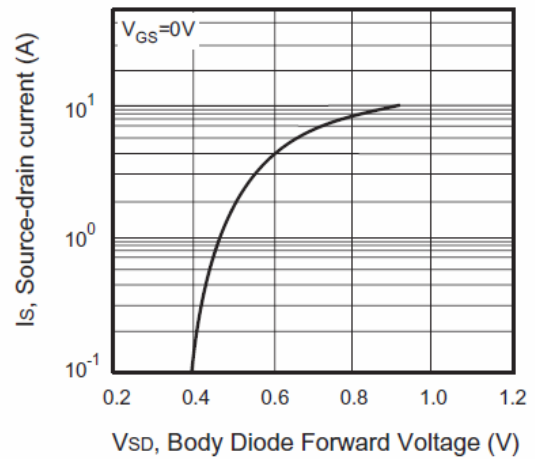
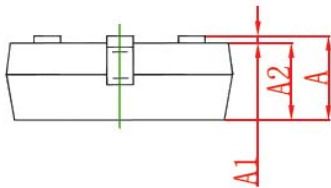
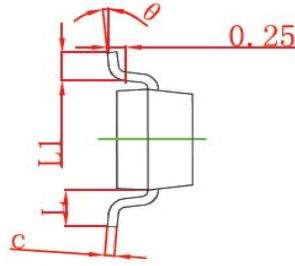
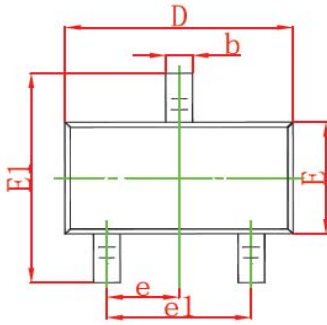


Figure 6. Body Diode Forward Voltage Variation with Source Current



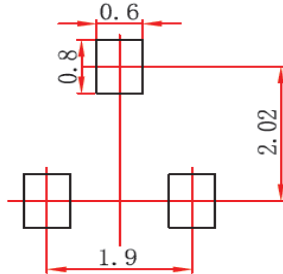
# YJL2300A

## ■ SOT-23 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

## ■ SOT-23 Suggested Pad Layout



- Note:
1. Controlling dimension: in millimeters.
  2. General tolerance:  $\pm 0.05\text{mm}$ .
  3. The pad layout is for reference purposes only.



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